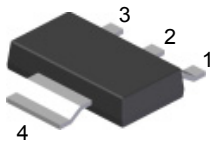
NEW PRODUCT

DZT591C

PNP SURFACE MOUNT TRANSISTOR

Features

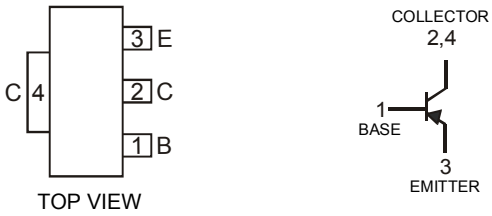
- Epitaxial Planar Die Construction
- Complementary NPN Type Available (DZT491)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 3)**



SOT-223

Mechanical Data

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish - Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.115 grams (approximate)



Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Continuous Current (Note 3)	I_C	-1	A
Peak Collector Current	I_{CM}	-2	A
Base Current	I_B	-200	mA
Power Dissipation (Note 3)	P_d	1	W
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 4)						
Collector-Base Cutoff Current	I_{CBO}	—	—	-100	nA	V_{CB} = -60V
Emitter-Base Cutoff Current	I_{EBO}	—	—	-100	nA	V_{EB} = -4V
Collector-Emitter Cutoff Current	I_{CES}	—	—	-100	nA	V_{CES} = -60V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-80	—	—	V	I_C = 100μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-60	—	—	V	I_C = 10mA
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5	—	—	V	I_E = 100μA
ON CHARACTERISTICS (Note 4)						
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	—	-0.3	V	I_C = -500mA, I_B = -50mA
		—	—	-0.6	V	I_C = -1A, I_B = -100mA
DC Current Gain	h_{FE}	100	—	—	—	V_{CE} = -5V, I_C = -1mA
		100	—	300	—	V_{CE} = -5V, I_C = -500mA
		80	—	—	—	V_{CE} = -5V, I_C = -1A
		15	—	—	—	V_{CE} = -5V, I_C = -2A
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	—	-1.2	V	I_C = -1A, I_B = -100mA
Base-Emitter Turn-On Voltage	$V_{BE(on)}$	—	—	-1	V	I_C = -1A, V_{CE} = -5V
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product	f_T	150	—	—	MHz	V_{CE} = -10V, I_C = -50mA, f = 100MHz
Output Capacitance	C_{obo}	—	13	—	pF	V_{CB} = -10V, f =1MHz

Notes:
1. No purposefully added lead.
2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
3. Device mounted on FR-4 PCB, pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
4. Measured under pulsed conditions. Pulse width = 300ms. Duty cycle ≤ 2%.

NEW PRODUCT

Typical Characteristics @T_A = 25°C unless otherwise specified

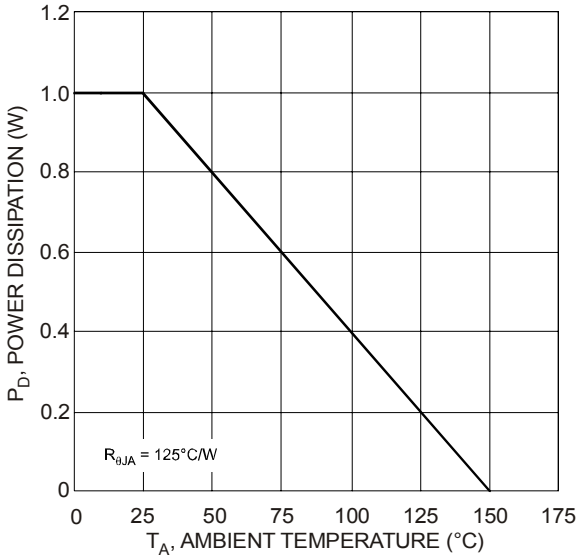


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

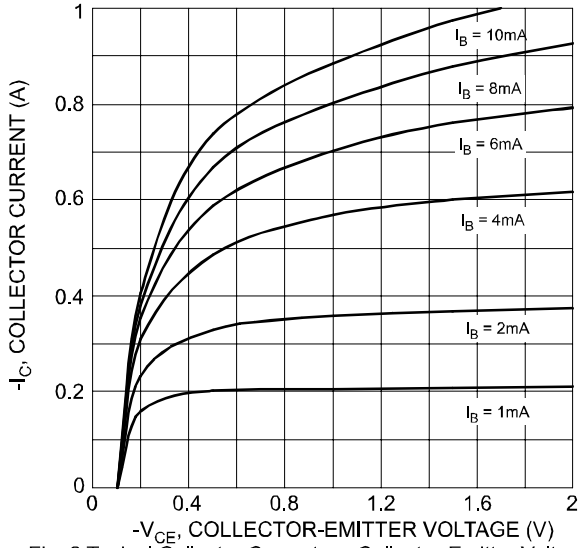


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

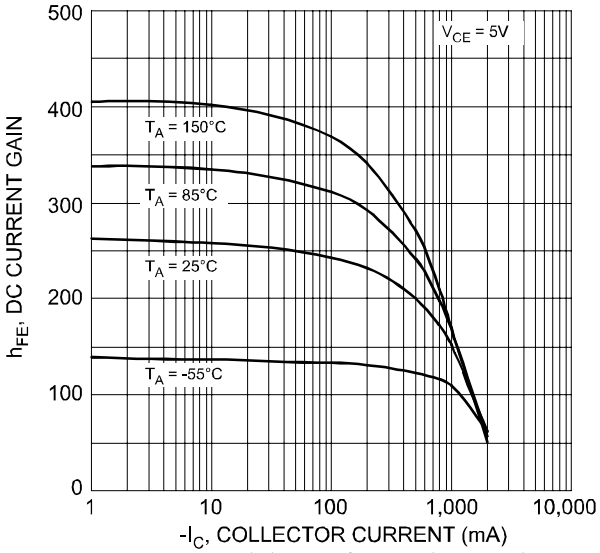


Fig. 3 Typical DC Current Gain vs. Collector Current

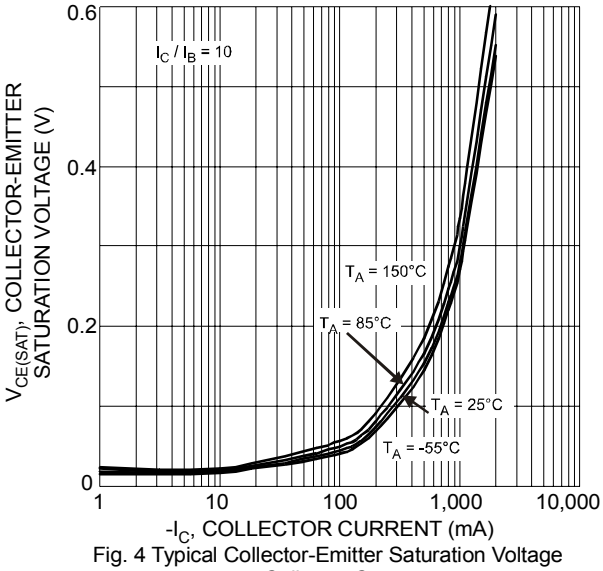


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

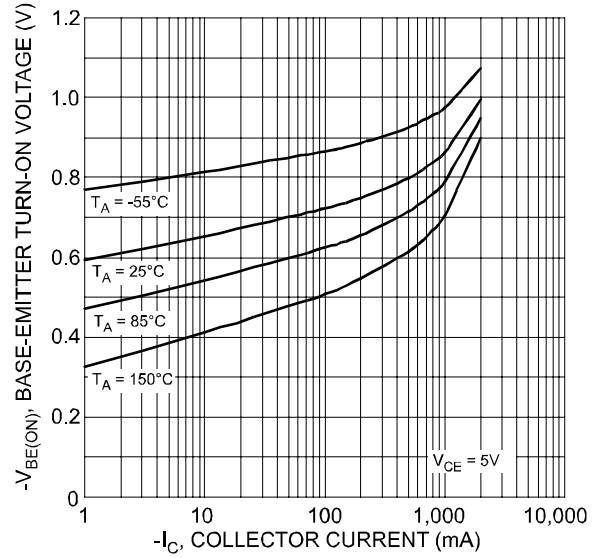


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

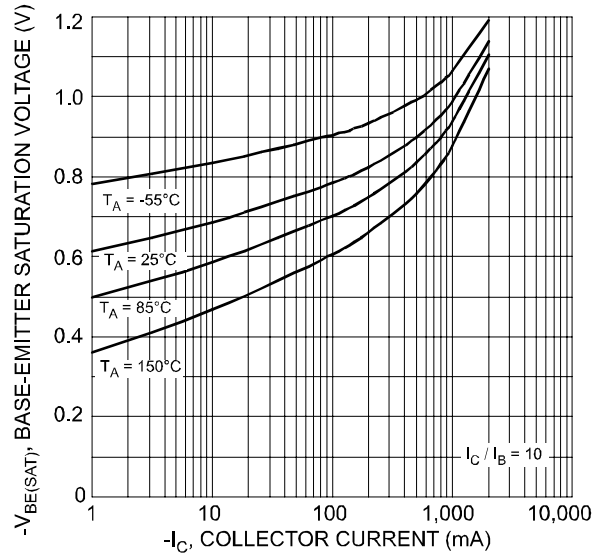


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

NEW PRODUCT

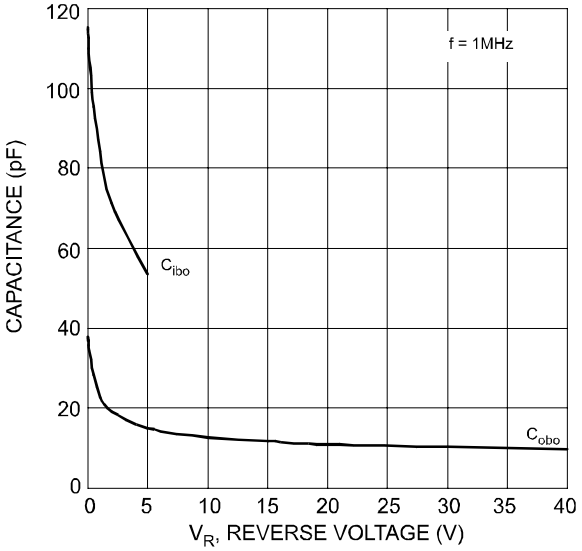


Fig. 7 Typical Capacitance Characteristics

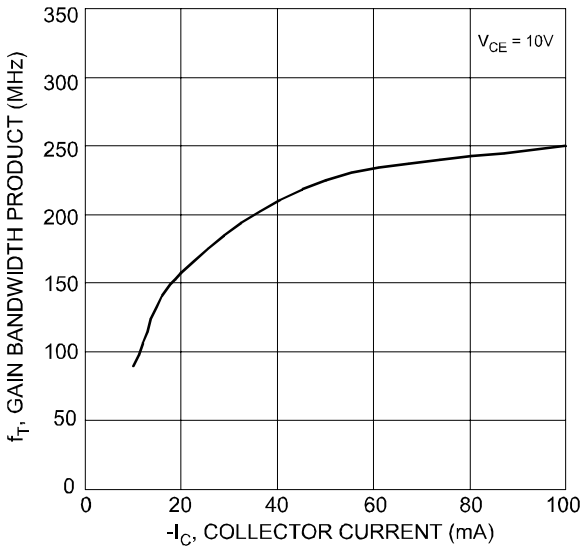


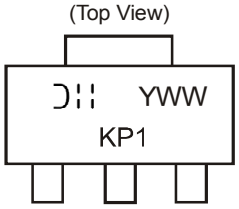
Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
DZT591C-13	SOT-223	2500/Tape & Reel

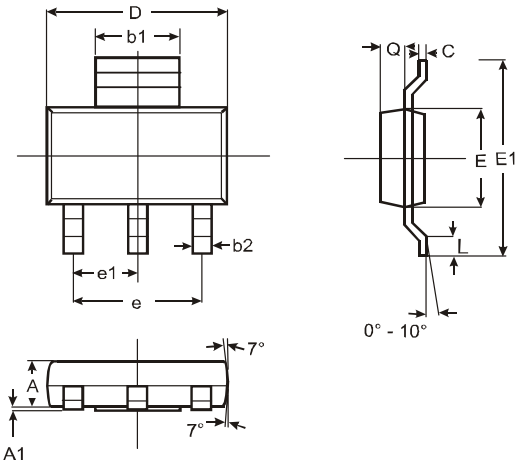
Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



= Manufacturer's code marking
KP1 = Product type marking code
YWW = Date code marking
Y = Last digit of year ex: 7 = 2007
WW = Week code 01 - 52

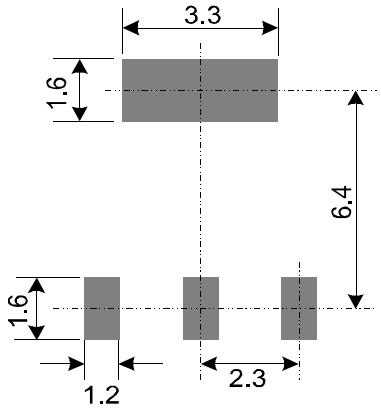
Package Outline Dimensions



SOT-223			
Dim	**Min**	**Max**	**Typ**
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b1	2.90	3.10	3.00
b2	0.60	0.80	0.70
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	—	—	4.60
e1	—	—	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

NEW PRODUCT

Suggested Pad Layout: (Based on IPC-SM-782)



(Unit: mm)

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